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OF

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Application Number	10/712,460
Filing Date	November 13, 2003
Applicant(s)	Chia-Lin Chen, et al.
Art Unit	4746 2826
Examiner Name	To Be Determined C. Everhart
Attorney Docket Number	24061.42 (TSMC2002-1015)

U. S. PATENT DOCUMENTS

Examiner's Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee, or Applicant of Cited Document
CME	AA	2002/0009900	01/24/02	Tay et al.
	AB	5,371,396	12/06/94	Vinal et al.
	AC	5,521,127	05/28/96	Hori et al.
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FOREIGN PATENT DOCUMENTS

Examiner's Initials	Cite No.	Foreign Patent Document (Country Code - Number - Kind)	Publication Date MM-DD-YYYY	Patentee or Applicant of Cited Document	Translation Y/N

OTHER PRIOR ART

Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume, issue number(s), publisher, city/country where published.
CME	AY	ARNUAD, F., ET AL., "Gate Oxide Process Impact on RNCE for Advanced CMOS Transistors", September 2002, ESSDERC '02, Firenze Italy, 21 pages.
CME	AZ	LI, GENE, "Total Solutions for Front-End Thermal Processing", Foresight, May 2001, Pages 41-45.
CME	BA	ZONCA, R., ET AL., "Ultra Thin NO ₂ /N ₂ O Oxynitride Dielectric for Advanced Flash Memory Application: Single Wafer and Batch Technology", 6 pages.
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CME	BC	"Technology Challenges for 100nm and Beyond Transistor and Capacitor Fabrication: Fig. 8", World Wide Web http://www.future-fab.com/assets/images/FFI11E1104F8.htm , printed on February 18, 2003, 1 page.

Examiner Signature	<i>C. Everhart</i>	Date Considered	10/15/04
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[illegible]

NON-PATENT LITERATURE		
Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume-issue number(s), publisher, city/country where published
NAME	AC	Decoupled Plasma Nitridation (DPN), May 2001, Foresight, Pages 43-45.

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